

P-Channel 30V Trench MOSFET, ESD Protection

General Description

The LV20P03K is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance

Features

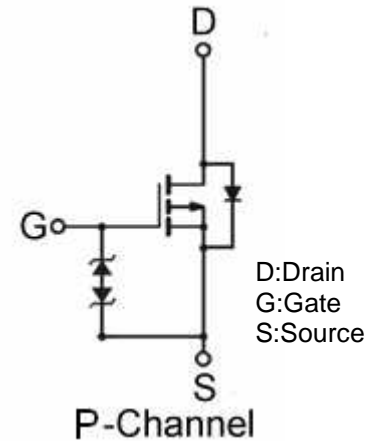
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- Marking: LV20P03K
- ESD Protection
- Qualified to MIL-STD-750E
- Moisture Sensitivity Level 3 per J-STD-020
- Weight: 0.08g
- RoHS Compliant



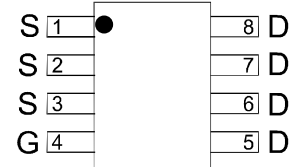
Application

- Power Management in Notebook
- Battery Powered System
- Load Switch
- DC/DC Converter

$B_{VDSS} = -30V$,
 $R_{DS(ON)} \leq 20m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} \leq 30m\Omega @ V_{GS} = -4.5V$
 $I_D = -8.8A$



(SOP-8)
Top View



Absolute Maximum Ratings ($T_A=25^\circ C$ Unless Otherwise Noted)

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	$T_A=25^\circ C$	-8.8
		$T_A=70^\circ C$	-7.1
Pulsed Drain Current	I_{DM}	-35	A
Power Dissipation ¹	P_D	$T_A=25^\circ C$	2.5
		$T_A=70^\circ C$	1.6
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Thermal Characteristics

PARAMETER	SYMBOL	TYP	UNIT
Thermal Resistance Junction-to-Ambient ¹	R_{thJA}	50	$^\circ C / W$

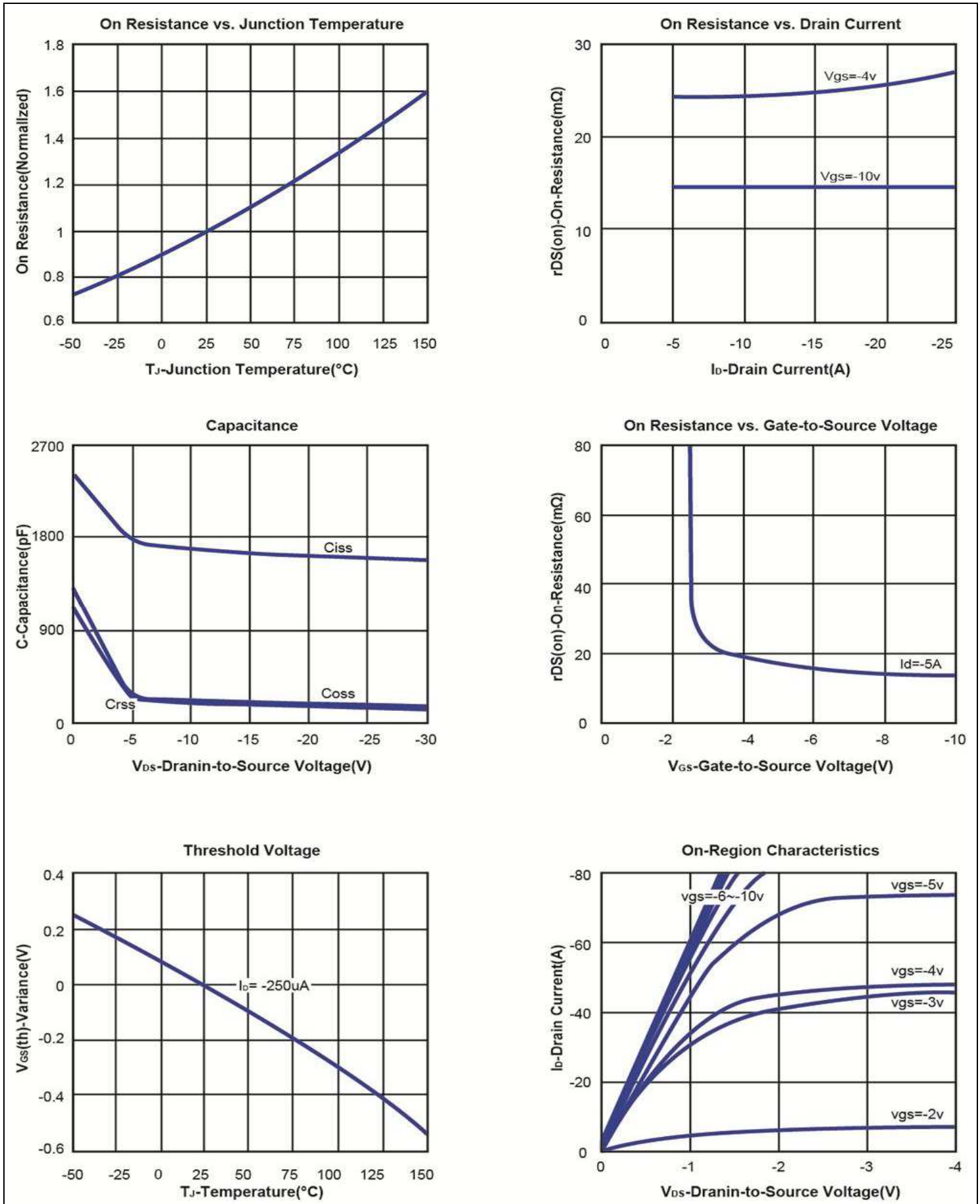
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Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	BV_{DSS}	-30	--	--	V
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	$V_{GS(th)}$	-0.8	--	-2	V
Gate-Source Leakage	$V_{DS}=0V, V_{GS}=\pm 16V$	I_{GSS}	--	--	± 10	μA
Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V$	I_{DSS}	--	--	-1	μA
Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-5A$	$R_{DS(ON)}$	--	14	20	$m\Omega$
	$V_{GS}=-4V, I_D=-5A$		--	24	30	
DYNAMIC						
Total Gate Charge	$V_{GS}=-10V, V_{DS}=-15V, I_D=-10A$	Q_g	--	41.1	--	nC
Gate-Source Charge		Q_{gs}	--	7.9	--	
Gate-Drain Charge		Q_{gd}	--	11.9	--	
Input Capacitance	$V_{GS}=0V, V_{DS}=-15V, F=1MHz$	C_{iss}	--	1644	--	pF
Output Capacitance		C_{oss}	--	205	--	
Reverse Transfer Capacitance		C_{rss}	--	178	--	
Turn-On Delay Time	$V_{GS} = -10V, V_{DS} = -15V, R_G = 4.7\Omega, R_L=3\Omega, I_D=-5A$	$t_{d(on)}$	--	78	--	nS
Turn-On Rise Time		t_r	--	60.4	--	
Turn-Off Delay Time		$t_{d(off)}$	--	101	--	
Turn-Off Fall Time		t_f	--	31.6	--	
Source-Drain Diode						
Diode Forward voltage	$I_S=-10A, V_{GS}=0V$	V_{SD}	--	--	-1.2	V

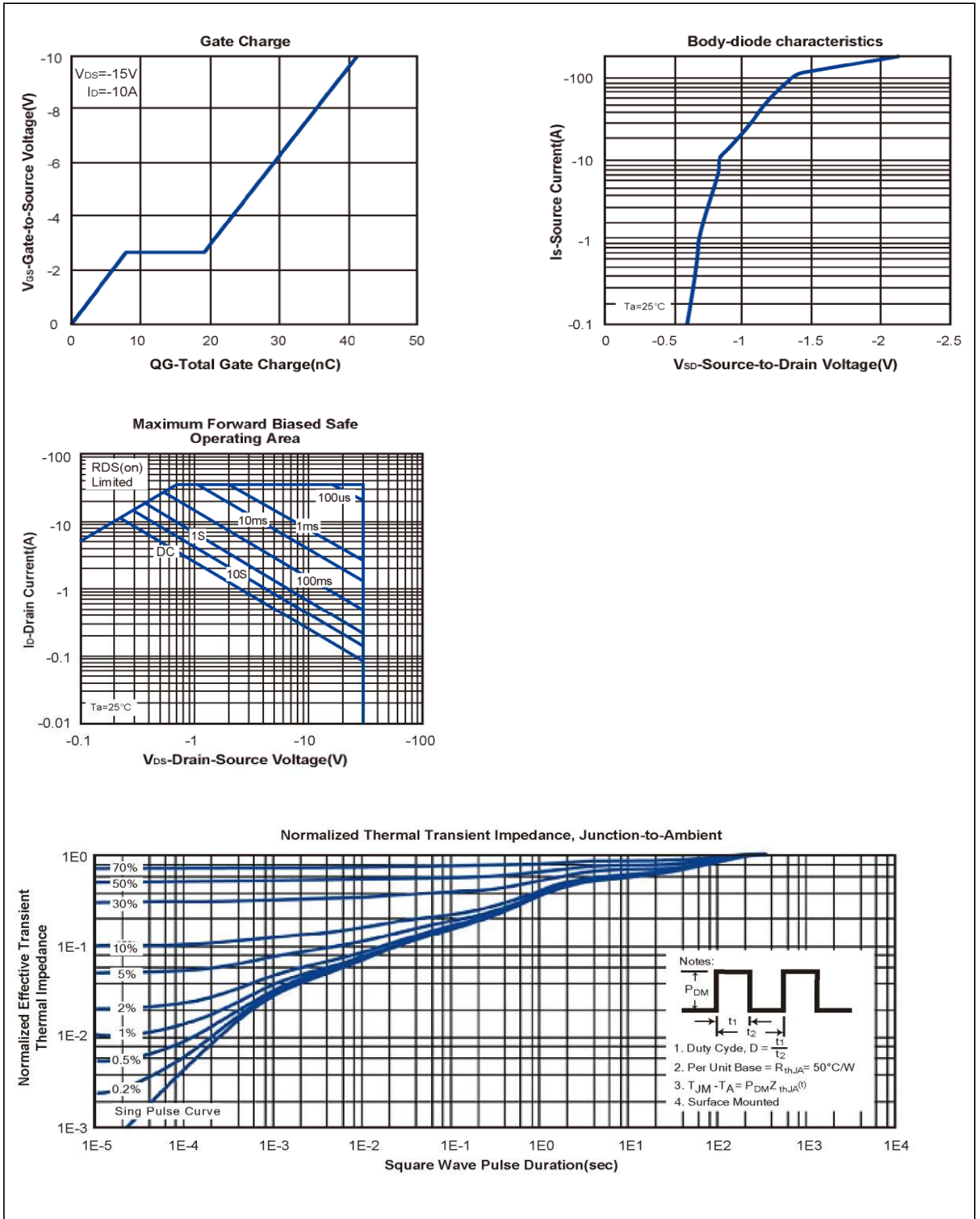
Notes:

- (1). The device mounted on 1in² FR4 board with 2 oz copper
- (2). Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, guaranteed by design, not subject to production testing.
- (3). LiteON Semiconductor reserves the right to improve product design, functions and reliability without notice

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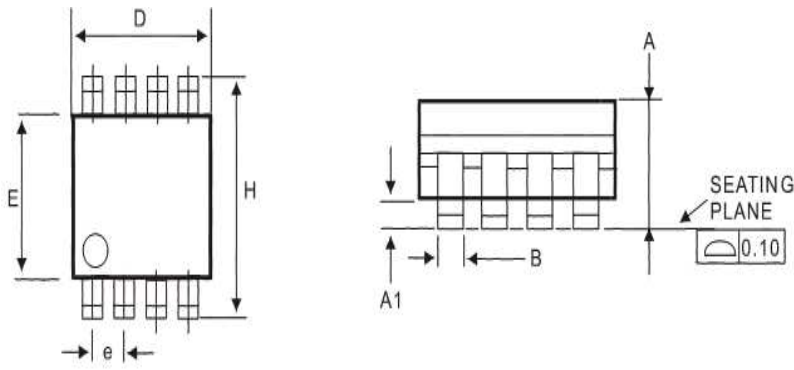
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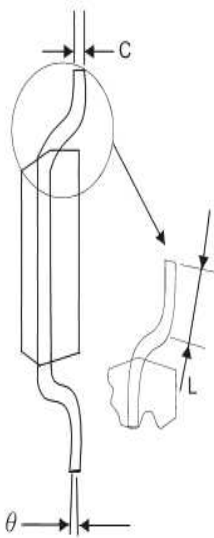
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Package Outline Dimension

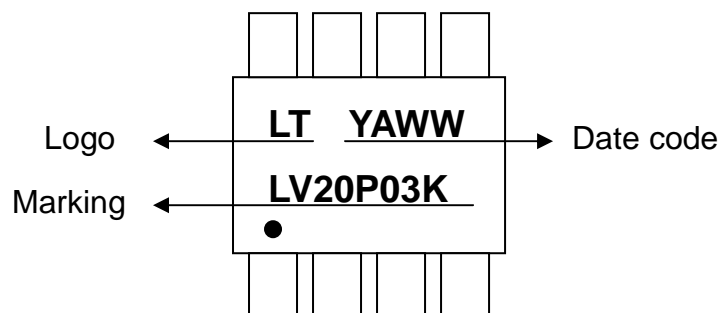
SOP-8



SOP-8		
DIM	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27BSC	
H	5.80	6.20
L	0.40	1.25
Θ	0°	7°
All Dimensions in millimeter		



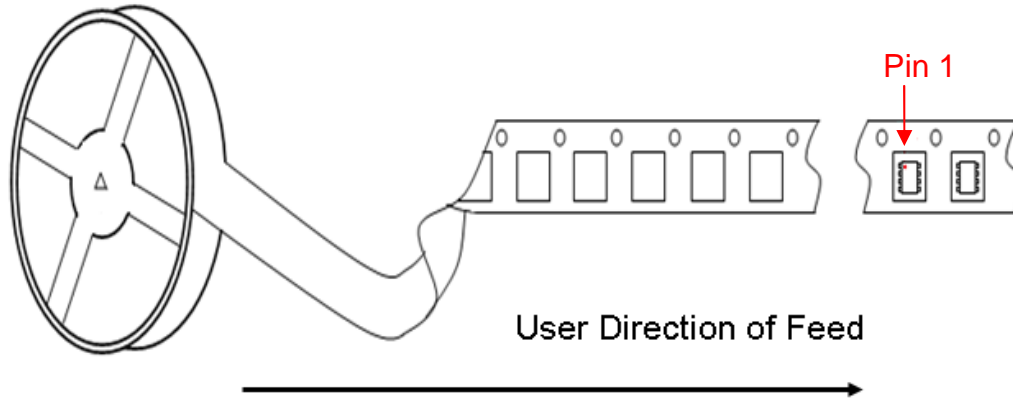
Marking information



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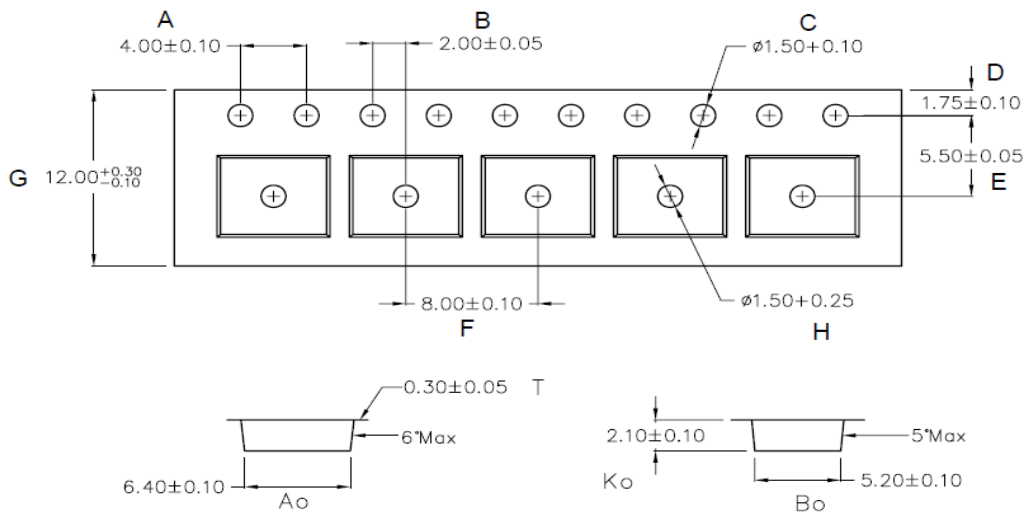
Packaging Information

Polar Units



DEVICE	Q'TY/REEL (PCS)	REEL DIA. (mm)	BOX SIZE (cm)	Q'TY/BOX (PCS)	CARTON SIZE (cm)	Q'TY/CARTON (PCS)
LV20P03K	2500	330	36.5x34x6	5K	39x39x38	30K

Embossed Carrier Dimensions Information



TAPE SIZE	A	B	C	D	E	F	Unit
12mm	4.00±0.10	2.00±0.05	1.50±0.10	1.75±0.10	5.50±0.05	8.00±0.10	mm
	G	H	T	Ao	Ko	Bo	
	12.00+0.30/-0.10	ø1.50+0.25	0.30±0.05	6.40±0.10	2.10±0.10	5.20±0.10	

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